

Spin-dependent tunneling conductance of Fe|MgO|Fe sandwich

Physical Review B

63,

DOI: [10.1103/physrevb.63.054416](https://doi.org/10.1103/physrevb.63.054416)

Citation Report

#	ARTICLE	IF	CITATIONS
1	Large magnetoresistance in Fe/MgO/FeCo(001) epitaxial tunnel junctions on GaAs(001). <i>Applied Physics Letters</i> , 2001, 79, 1655-1657.	1.5	229
2	Sign reversal of spin polarization in Co/Ru/Al ₂ O ₃ /Comagnetic tunnel junctions. <i>Physical Review B</i> , 2001, 64, .	1.1	50
3	Atomic and electronic structure of Co/SrTiO ₃ /Comagnetic tunnel junctions. <i>Physical Review B</i> , 2001, 65, .	1.1	96
4	First-principles Modeling of Co/SrTiO ₃ /Co Magnetic Tunnel Junctions. <i>Materials Research Society Symposia Proceedings</i> , 2001, 690, F2.6.1.	0.1	1
5	Epitaxial Fe/MgO heterostructures on GaAs(001). <i>Journal of Crystal Growth</i> , 2001, 226, 223-230.	0.7	36
6	Scattering of surface-state electrons by the monatomic step in Fe(001): Differential conductivity imaging by scanning tunneling microscopy. <i>Physical Review B</i> , 2001, 65, .	1.1	13
7	Integration over two-dimensional Brillouin zones by adaptive mesh refinement. <i>Physical Review B</i> , 2001, 64, .	1.1	18
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853	13	2.0
855	0	1.2
856	3	1.2
857	92	0.7
858	8	1.1
859	927	1.2
860		1.1
861	23	1.1
862	118	1.6
863	22	1.1
864	4	0.4
865	26	0.7
866	10	1.0
867	29	1.6
868	59	1.1
869	7	0.9

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